

3CG110,3CG102**PNP Silicon High Frequency Low Power Transistor****Features:**

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit. Make up push pull amplifying circuit with NPN.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							
			3CG110			3CG102				
			A	B	C	A	B	C	D	
Total Dissipation	P_{tot}	mW	300 (Ta=25°C)			150 (Ta=25°C)				
Max. Collector Current	I_{CM}	mA	50			25				
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	15	30	45	12	12	15	15	
			$I_C=0.1mA$							
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	$\geq 4 (I_E=0.1 mA)$							
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.3 ($I_C=30mA, I_B=3mA$)			0.6 ($I_C=10mA, I_B=1mA$)				
C-E Leakage Current	I_{CEO}	uA	0.1 ($V_{CE}=10V$)							
DC Current Gain	h_{FE}		25~~270 ($V_{CE}=10V, I_C=10mA$)				25~~270 ($V_{CE}=10V, I_C=2mA$)			
Transition frequency	f_T	MHz	100			700	800	1000	1200	
			$(V_{CE}=10V, I_C=10mA, f=30MHz)$			$V_{CE}=10V, I_C=5mA, f=300MHz$				

 h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
h_{FE}	25~40	40~55	55~80	80~120	120~180	180~270

Outline and Dimensions: